TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC4S30F

EXCLUSIVE-OR GATE

TC4S30F contains one circuit of exclusive OR gate. Since the buffers of two stage inverters are provided for all the outputs, the input/output voltage characteristic has been improved and the noise immunity has been also improved. And increase of transmission time due to load capacity increase is kept minimum.

Wide variety of applications are offerred, such as digital comparators and parity circuits.

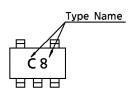
SSOP5-P-0.95

Weight: 0.016g (Typ.)

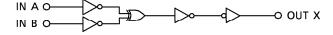
MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
DC Supply Voltage	v_{DD}	Vss - 0.5~Vss + 20	V
Input Voltage	v _{IN}	$V_{SS} - 0.5 \sim V_{DD} + 0.5$	>
Output Voltage	Vout	$V_{SS} - 0.5 \sim V_{DD} + 0.5$	>
DC Input Current	ΙΝ	± 10	mΑ
Power Dissipation	PD	200	mW
Operating Temperature Range	T _{opr}	- 40∼85	°C
Storage Temperature Range	T _{stg}	- 65~150	°C
Lead Temperature (10s)	TL	260	°C

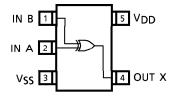
MARKING



LOGIC DIAGRAM



PIN ASSIGNMENT (TOP VIEW)



TRUTH TABLE

INF	OUTPUT	
Α	В	Х
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

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RECOMMENDED OPERATING CONDITIONS $(V_{SS} = 0V)$

CHARACTERISTIC	SYMBOL		MIN.	TYP.	MAX.	UNIT
DC Supply Voltage	V_{DD}	_	3	_	18	V
Input Voltage	V _{IN}		0	_	V_{DD}	V

STATIC ELECTRICAL CHARACTERISTICS $(V_{SS} = 0V)$

CHARACTERISTIC SYM-		TEST CONDITION	V _{DD} − 40°C		0°C	25°C			85°C		UNIT
CHARACTERISTIC	BOL	TEST CONDITION	(V)	MIN.	MAX.	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High-Level		_{OUT} <1μΑ	5	4.95	_	4.95	5.00	_	4.95	_	
Output Voltage	۷он	$V_{IN} = V_{SS}, V_{DD}$	10	9.95		9.95	10.00	—	9.95	_	
Output Voltage		VIN - 422, ADD	15	14.95	_	14.95	15.00	_	14.95	_	V
Low-Level		 l _{OUT} <1μΑ	5	_	0.05	_	0.00	l	 	0.05	Ū
Output Voltage	VOL	$V_{IN} = V_{SS}$, V_{DD}	10	_	0.05	_	0.00	l	—	0.05	
- Catput Voltage			15	_	0.05	_	0.00	0.05		0.05	
		V _{OH} = 4.6V	5	- 0.61		- 0.51	- 1.0	l	- 0.42		
Output High		$V_{OH} = 2.5V$	5	- 2.5		- 2.1	- 4.0	l	– 1.7		
Current	IOH	V _{OH} = 9.5V	10	- 1.5		- 1.3	- 2.2	ı	- 1.1		
Carrent		V _{OH} = 13.5V	15	- 4.0	_	- 3.4	- 9.0	—	- 2.8	_	
		$V_{IN} = V_{SS}, V_{DD}$									mΑ
		$V_{OL} = 0.4V$	5	0.61		0.51	1.2	l	0.42		ША
Output Low	lOL	V _{OL} = 0.5V	10	1.5		1.3	3.2	i	1.1	t	
Current	'OL	V _{OL} = 1.5V	15	4.0	_	3.4	12.0	—	2.8	_	
		$V_{IN} = V_{SS}$, V_{DD}									
		V _{OUT} = 0.5V, 4.5V	5	3.5	_	3.5	2.75	_	3.5		
Input High Voltage	\ \ \ \	V _{OUT} = 1.0V, 9.0V	10	7.0	_	7.0	5.5	_	7.0	_	
Imput High Voltage	VIH	V _{OUT} = 1.5V, 13.5V	15	11.0	_	11.0	8.25	—	11.0	_	
		l _{OUT} <1μΑ									v
		V _{OUT} = 0.5V, 4.5V	5	_	1.5	_	2.25	1.5	_	1.5	
Input Law Valtage	.,	V _{OUT} = 1.0V, 9.0V	10	_	3.0	_	4.5	3.0	 	3.0	
Input Low Voltage	V_{IL}	V _{OUT} = 1.5V, 13.5V	15	_	4.0	_	6.75	4.0	_	4.0	
		l _{OUT} <1μΑ									
Input H Level	ΊΗ	V _{IH} = 18V	18	_	0.1	_	10 ⁻⁵	ı	_	1.0	
Current L Level	IJL	V _{IL} = 0V	18	_	- 0.1	_	- 10 ^{- 5}	-0.1	—	- 1.0	μΑ
Quiescent			5	_	1	_	0.001	l		7.5	
Device Current	IDD	$V_{IN} = V_{SS}$, V_{DD}	10	_	2	—	0.002	l	—	15	μ A
Device Carrent			15	_	4	_	0.002	4	_	30	

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DYNAMIC ELECTRICAL CHARACTERISTICS (Ta = 25°C, V_{SS} = 0V, C_L = 50pF)

CHARACTERISTIC	SYMBOL	TEST CONDITION	V _{DD} (V)	MIN.	TYP.	MAX.	UNIT
Output Transition Time	,		5	_	70 25	200	
(Low to High)	t _{TLH}	_	10	_	35	100	
(Low to High)			15	_	30	80	
Output Transition Time (High to Low)	tTHL		5	_	70	200	ns
		_	10	_	35	100	
			15	_	30	80	
	4		5		90	280	
Propagation Delay Time	t _{pLH} t _{pHL}	_	10	_	45	130	ns
			15		35	100	
Input Capacitance	CIN	_		_	5	7.5	pF

CIRCUIT AND WAVEFORM FOR MEASUREMENT OF DYNAMIC CHARACTERISTICS

CIRCUIT WAVEFORM

